

UTC UNISONIC TECHNOLOGIES CO., LTD

UG5N120

Preliminary

Insulated Gate Bipolar Transistor

21A, 1200V NPT N-CHANNEL **IGBT WITH ANTI-PARALLEL** HYPERFAST DIODES

DESCRIPTION

The UTC UG5N120 is a NPT N-Channel IGBT, it uses UTC's advanced technology to provide the customers with a minimum on-state resistance, etc.

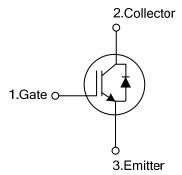
The UTC UG5N120 is suitable for AC and DC motor controls, power supplies, and drivers for solenoids, relays and contactors, etc.

FEATURES

* Low conduction loss

* Short circuit rating

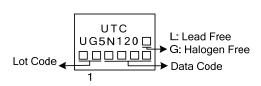
SYMBOL

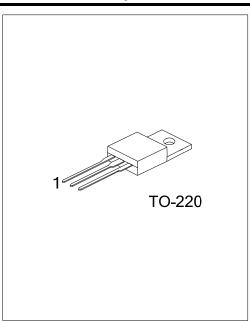




Ordering Number		Package	Pin Assignment			Dooking		
Lead Free	Halogen Free	Fackage	1	2	3	Packing		
UG5N120L-TA3-T	UG5N120G-TA3-T	TO-220	G	С	Е	Tube		
Note: Pin Assignment: G: Gate C: Collector E: Emitter								
	 (1) T: Tube (2) TA3: TO-220 (3) L: Lead Free, G: Halogen Free and Lead Free 							

MARKING





■ ABSOLUTE MAXIMUM RATING (T_C=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector to Emitter Voltage	BV _{CES}	1200	V
Gate-Emitter Voltage	V _{GES}	±20	V
Gate to Emitter Voltage Pulsed	V _{GEM}	±30	V
Collector Current Continuous	- I _C	21	А
T _c =110°C		10	А
Collector Current Pulsed (Note 1)	I _{CM}	40	А
Power Dissipation Total at T _C =25°C	PD	167	W
Power Dissipation Derating T _C >25°C		1.33	W/°C
Short Circuit Withstand Time (Note 2) at V _{GE} =15V	t _{sc}	8	μs
Short Circuit Withstand Time (Note 2) at V _{GE} =12V	t _{sc}	15	μs
Operating Junction Temperature Range	TJ	-55~+150	°C
Storage Temperature Range	T _{STG}	-55~+150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Pulse width limited by maximum junction temperature.

3. I_{CE} =10A, L=400µH, T_J=25°C.

4. V_{CE(PK)}=840V, T_J=125°C, R_G=25Ω.

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Case	θ _{JC}	0.75	°C/W	

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT
Collector to Emitter Breakdown Voltage	BV _{CES}	I _C =250μA, V _{GE} =0V		1200			V
Collector to Emitter Leakage Current	I _{CES}	V _{CE} =1200V	T _C =25°C			250	μA
			T _C =125°C		100		μA
			T _C =150°C			1.5	mA
Collector to Emitter Saturation Voltage	V _{CE(SAT)}	I _C =5A, V _{GE} =15V	T _C =25°C		2.45	2.7	V
			T _C =150°C		3.7	4.2	V
Gate to Emitter Threshold Voltage	V _{GE(TH)}	I _C =45µA, V _{CE} =V _{GE}		6.0	6.8		V
Gate to Emitter Leakage Current	I _{GES}	V _{GE} =±20V				±250	nA
Switching SOA	SSOA	T_J =150°C, R_G =25 Ω , V_{GE} =15V, L=5mH, $V_{CE(PK)}$ =1200V		30			А
							^
Gate to Emitter Plateau Voltage	V _{GEP}	I _C =5A, V _{CE} =600V			10.5		V
On-State Gate Charge	Q _{G(ON)}	$I_{C}=5A$. $V_{CF}=600V$	V _{GE} =15V		53	65	nC
			V _{GE} =20V		60	72	nC
Current Turn-On Delay Time	t _{d(ON)}	IGBT and Diode at T _{.I} =25°C			220		ns
Current Rise Time	t _{rl}		0		360		ns
Current Turn-Off Delay Time	t _{d(OFF)}	I _{CE} =1.0A, V _{CE} =30V, V _{GE} =15V, -R _G =25Ω			320		ns
Current Fall Time	t _{fl}	NG-2032			120		ns



Preliminary

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